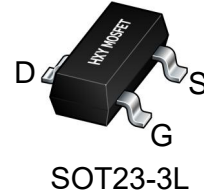




## Description

The SSM3J332R uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

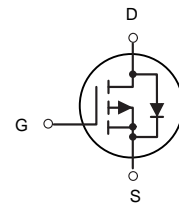


## General Features

$V_{DS} = -30V$   $I_D = -4.2A$   
 $R_{DS(ON)} < 54m\Omega @ V_{GS}=10V$   
 $R_{DS(ON)} < 77m\Omega @ V_{GS}=4.5V$

## Application

Battery protection  
Load switch  
Uninterruptible power supply



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SSM3J332R	SOT23-3L	X1KX	3000

## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	-4.2	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	-30	A
$P_D$	Maximum Power Dissipation	1.2	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	104	$^\circ C/W$



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	46	54	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	58	77	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		74	130	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4.2A	-	10	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	880	-	PF
Output Capacitance	C <sub>OSS</sub>		-	105	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	65	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-4.2A V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω	-	7	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	3	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.2A, V <sub>GS</sub> =-4.5V	-	8.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	2.7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-4.2A	-	-	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



### Typical Electrical and Thermal Characteristics

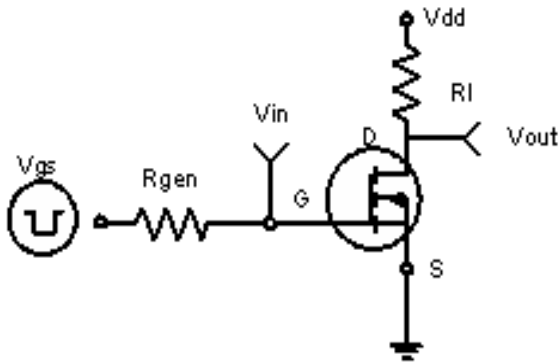


Figure 1: Switching Test Circuit

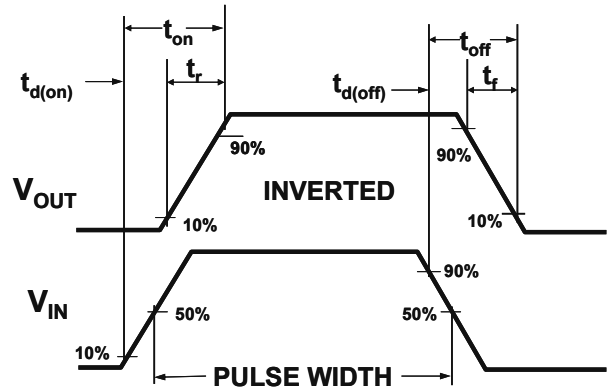
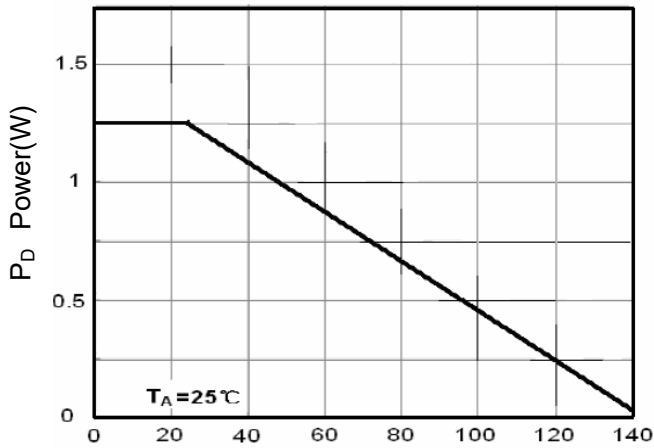
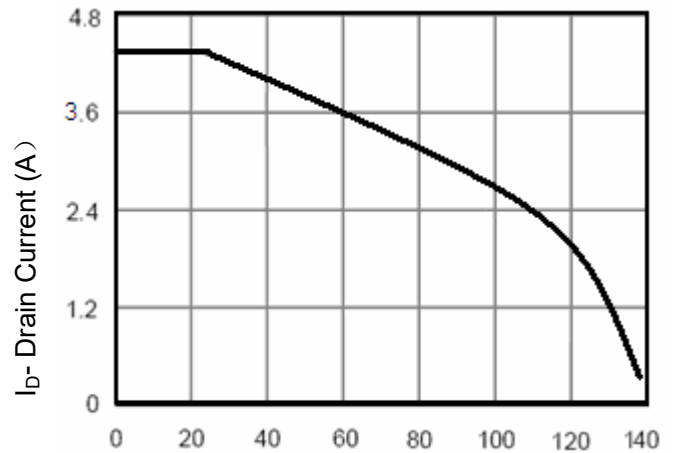


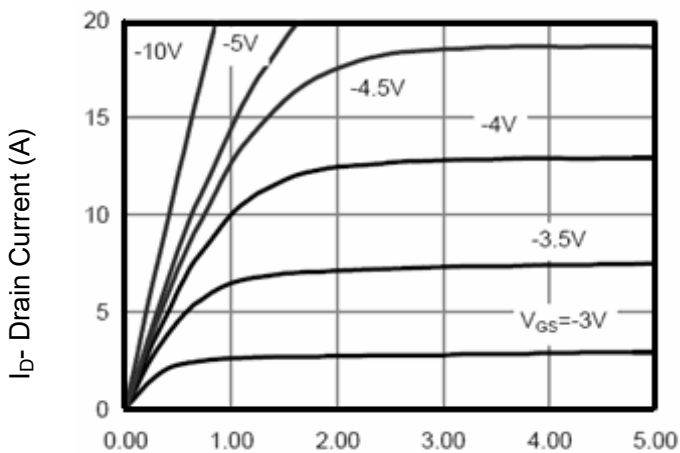
Figure 2: Switching Waveforms



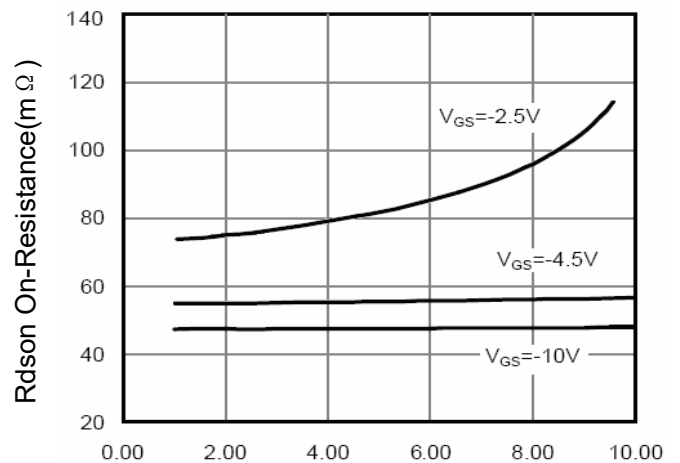
T<sub>J</sub>-Junction Temperature(°C)  
Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)  
Figure 4 Drain Current



V<sub>ds</sub> Drain-Source Voltage (V)  
Figure 5 Output Characteristics



ID- Drain Current (A)  
Figure 6 Drain-Source On-Resistance

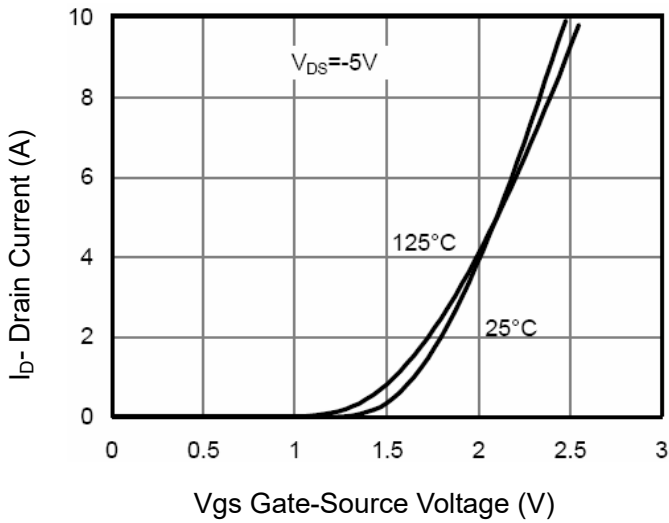


Figure 7 Transfer Characteristics

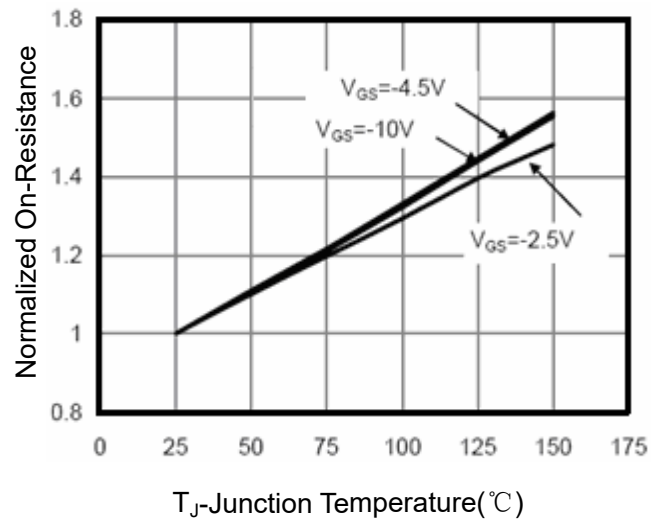


Figure 8 Drain-Source On-Resistance

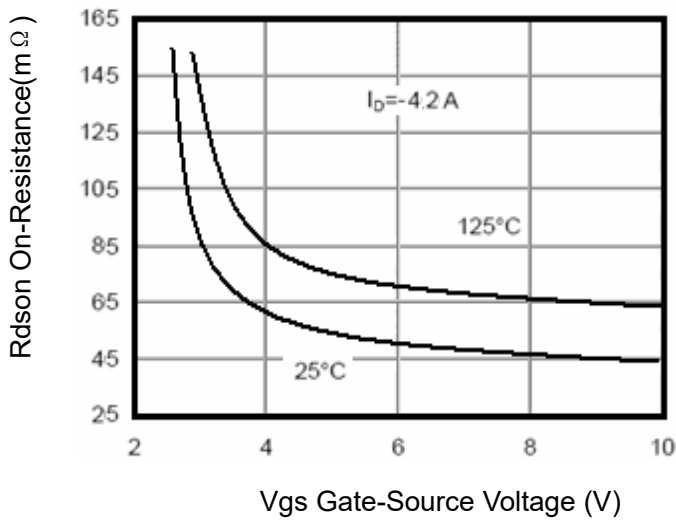


Figure 9 Rdson vs Vgs

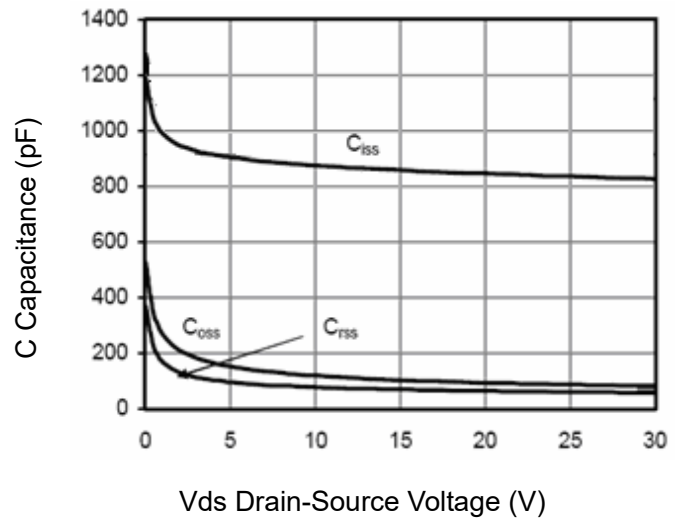


Figure 10 Capacitance vs Vds

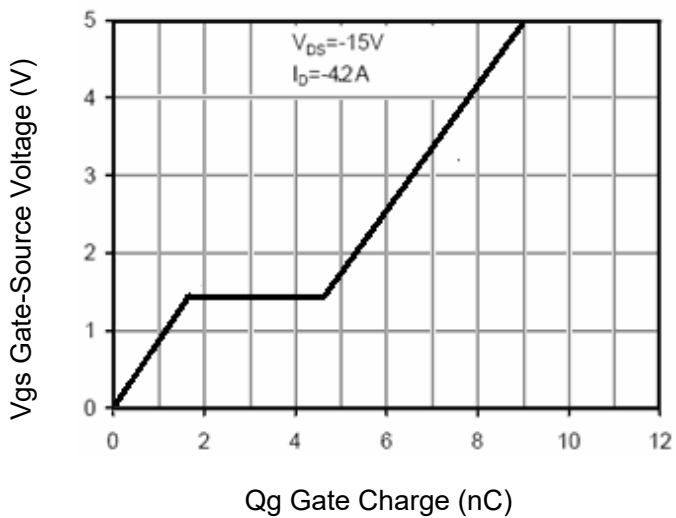


Figure 11 Gate Charge

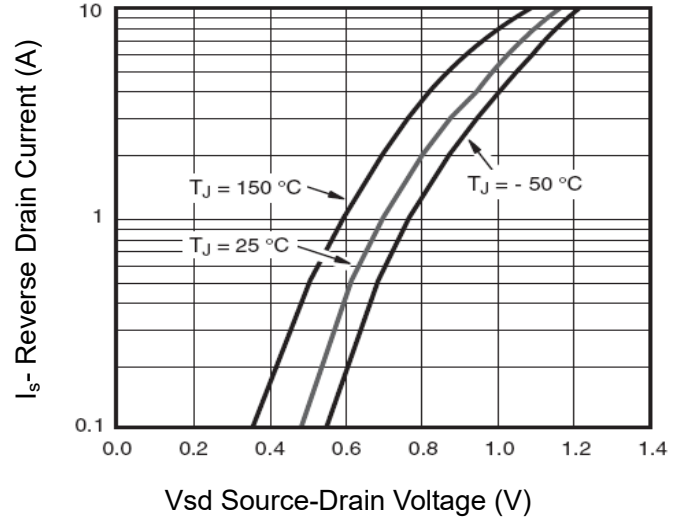
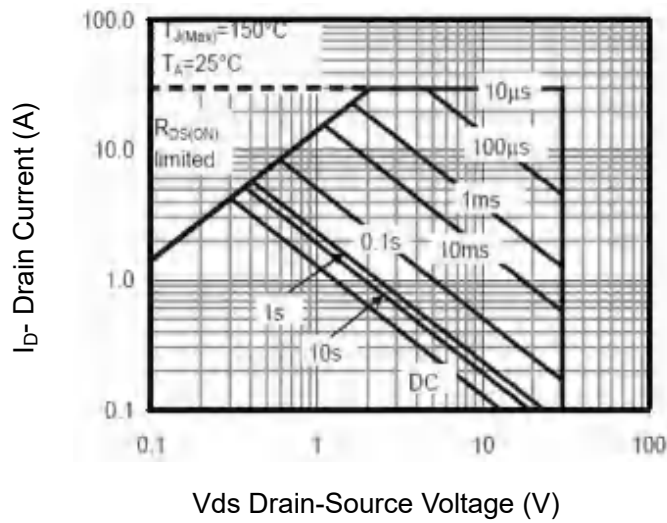
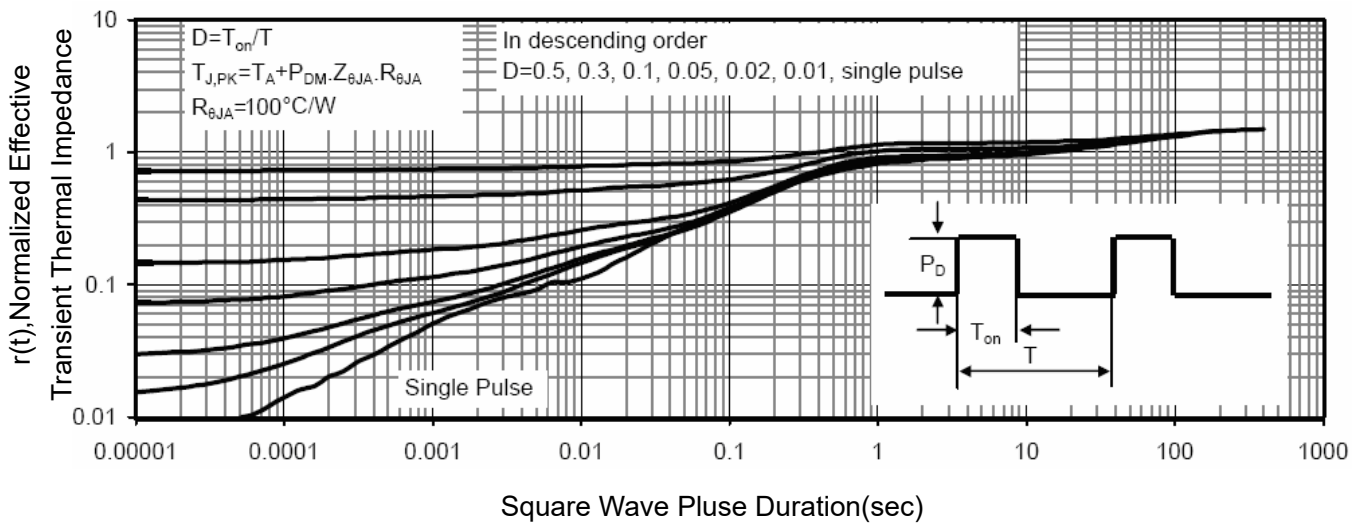


Figure 12 Source- Drain Diode Forward



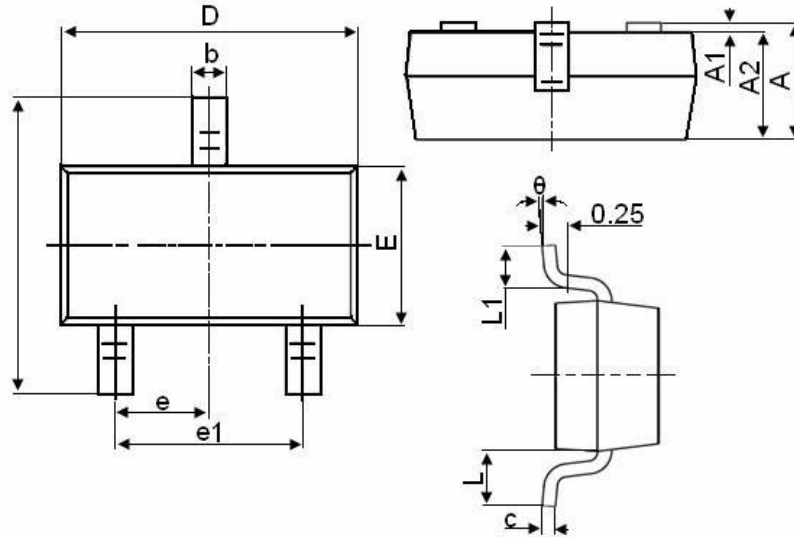
Vds Drain-Source Voltage (V)  
Figure 13 Safe Operation Area



Square Wave Pluse Duration(sec)  
Figure 14 Normalized Maximum Transient Thermal Impedance



### SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
$\theta$	0°	8°



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